

IRFS4321TRLPBF-VB Datasheet

N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY

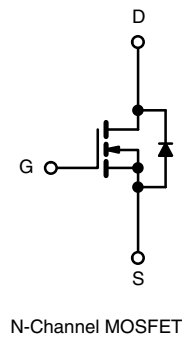
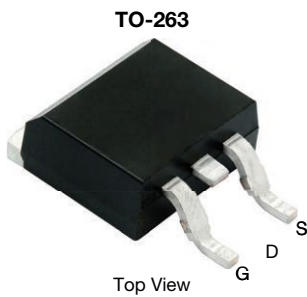
| V_{DS} (V) | $R_{DS(on)}$ (Ω) MAX. | I_D (A) | Q_g (TYP.) |
|--------------|--------------------------------|-----------|--------------|
| 150 | 0.0075 at $V_{GS} = 10$ V | 128 | 63 nC |
| | 0.0084 at $V_{GS} = 7.5$ V | 119 | |

FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization:



RoHS
COMPLIANT
HALOGEN
FREE



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier
- Battery management

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--------------------------------------------------|----------------|----------------|------|
| Drain-Source Voltage | V_{DS} | 150 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | A |
| | | $T_C = 125$ °C | |
| Pulsed Drain Current ($t = 100$ μ s) | I_{DM} | 240 | |
| Avalanche Current | I_{AS} | 60 | |
| Single Avalanche Energy ^a | E_{AS} | 180 | mJ |
| Maximum Power Dissipation ^a | P_D | $T_C = 25$ °C | W |
| | | $T_C = 125$ °C | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +175 | °C |

THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | LIMIT | UNIT |
|----------------------------------------------|------------|-------|------|
| Junction-to-Ambient (PCB Mount) ^c | R_{thJA} | 40 | °C/W |
| Junction-to-Case (Drain) | R_{thJC} | 0.4 | |

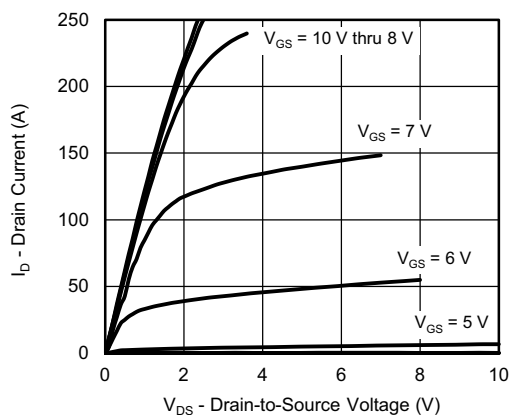
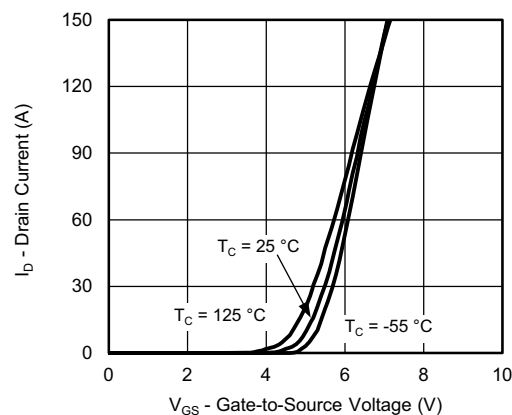
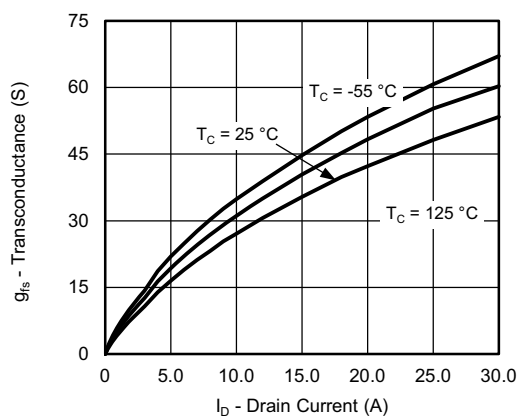
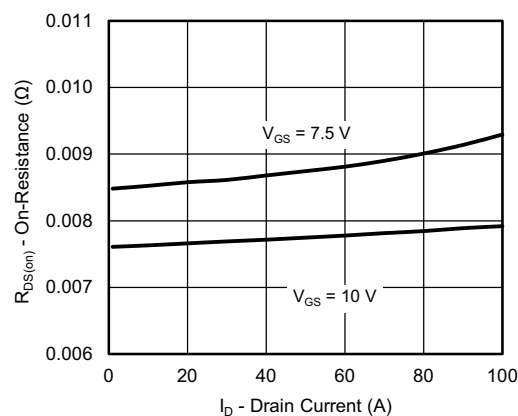
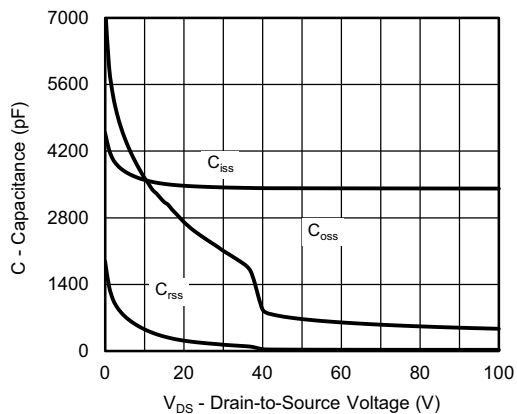
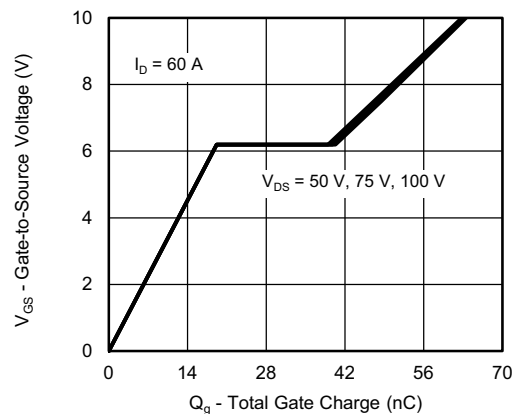
Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

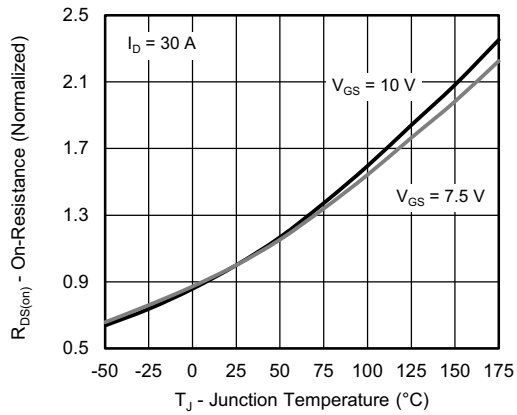
| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|-------------------------------------------------------------------------------------------|----------------------|-------------------------------------------------------------------------------------------------------------------------|------|--------|-------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 150 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 2 | - | 5 | |
| Gate-Body Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | - | - | ± 250 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 150 V, V _{GS} = 0 V | - | - | 1 | μA |
| | | V _{DS} = 150 V, V _{GS} = 0 V, T _J = 125 °C | - | - | 100 | |
| | | V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C | - | - | 2 | mA |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≥ 10 V, V _{GS} = 10 V | 90 | - | - | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V, I _D = 30 A | - | 0.0075 | - | Ω |
| | | V _{GS} = 7.5 V, I _D = 30 A | - | 0.0084 | - | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 15 V, I _D = 30 A | - | 52 | - | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0 V, V _{DS} = 75 V, f = 1 MHz | - | 3425 | - | pF |
| Output Capacitance | C _{oss} | | - | 535 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 26 | - | |
| Total Gate Charge ^c | Q _g | V _{DS} = 75 V, V _{GS} = 10 V, I _D = 60 A | - | 63 | 95 | nC |
| Gate-Source Charge ^c | Q _{gs} | | - | 19.5 | - | |
| Gate-Drain Charge ^c | Q _{gd} | | - | 20.5 | - | |
| Gate Resistance | R _g | f = 1 MHz | 1.5 | 3 | 5 | Ω |
| Turn-On Delay Time ^c | t _{d(on)} | V _{DD} = 75 V, R _L = 1.25 Ω I _D ≅ 60 A, V _{GEN} = 10 V, R _g = 1 Ω | - | 15 | 30 | ns |
| Rise Time ^c | t _r | | - | 114 | 220 | |
| Turn-Off Delay Time ^c | t _{d(off)} | | - | 28 | 56 | |
| Fall Time ^c | t _f | | - | 8 | 16 | |
| Drain-Source Body Diode Ratings and Characteristics ^b (T _C = 25 °C) | | | | | | |
| Pulsed Current (t = 100 μs) | I _{SM} | | - | - | 240 | A |
| Forward Voltage ^a | V _{SD} | I _F = 30 A, V _{GS} = 0 V | - | 0.73 | 1.2 | V |
| Reverse Recovery Time | t _{rr} | I _F = 30 A, di/dt = 100 A/μs | - | 110 | 220 | ns |
| Peak Reverse Recovery Charge | I _{RM(REC)} | | - | 10 | 20 | A |
| Reverse Recovery Charge | Q _{rr} | | - | 0.5 | 1 | μC |

Notes

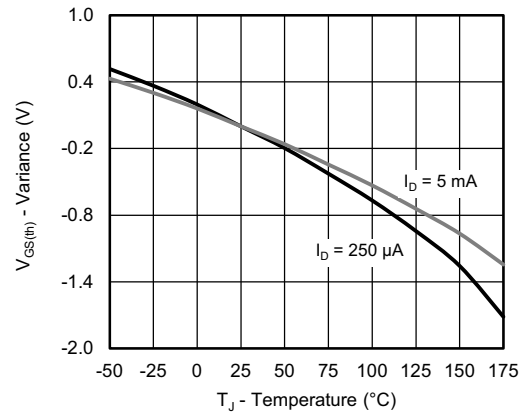
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

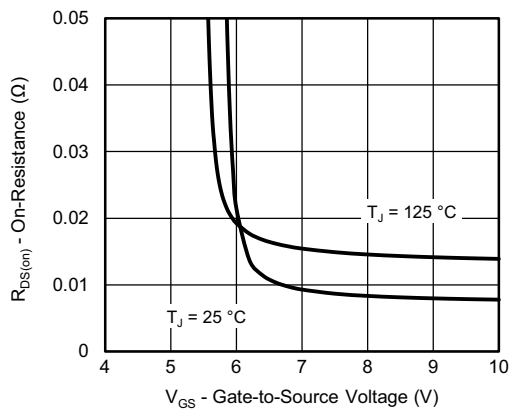
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



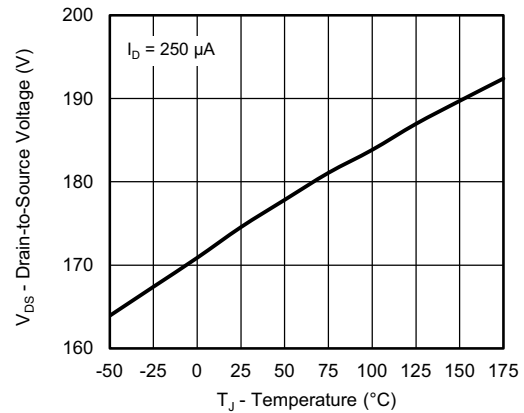
On-Resistance vs. Junction Temperature



Threshold Voltage



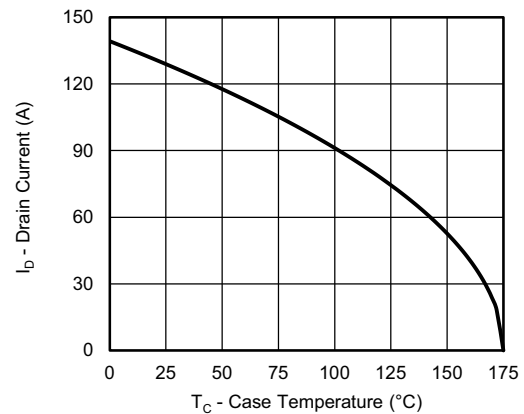
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

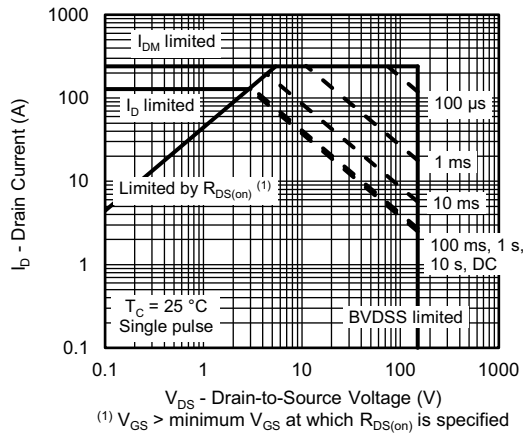


Source Drain Diode Forward Voltage

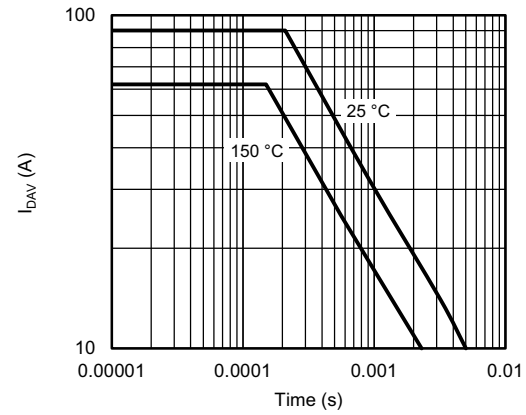


Current De-Rating

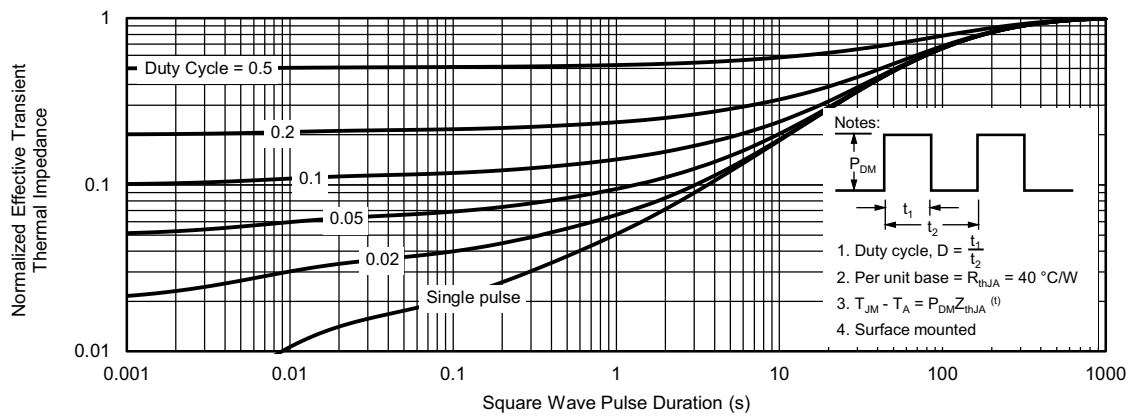
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



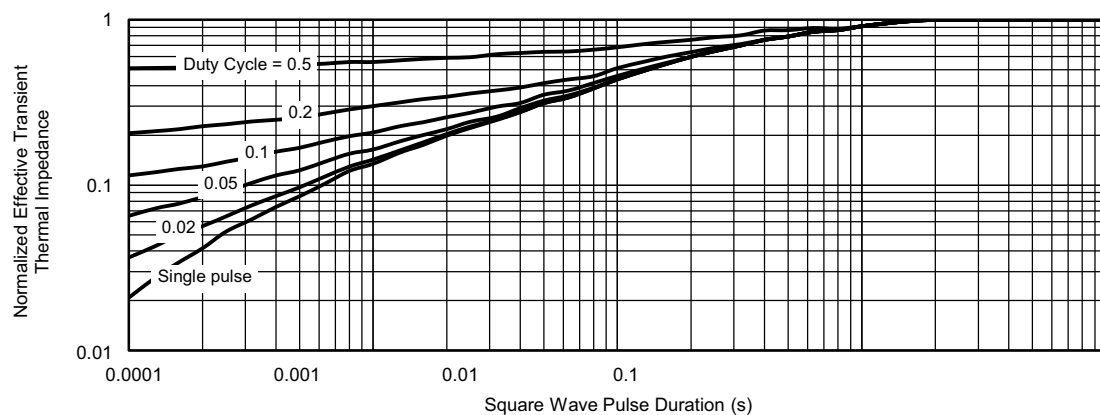
Safe Operating Area



I_{DAV} vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

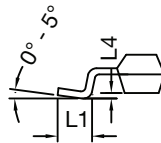
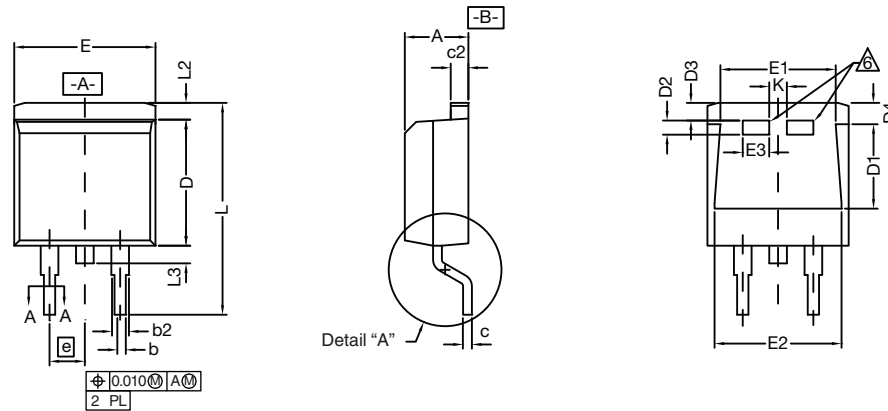
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Case

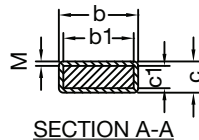
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-263 (D²PAK): 3-LEAD




DETAIL A (ROTATED 90°)



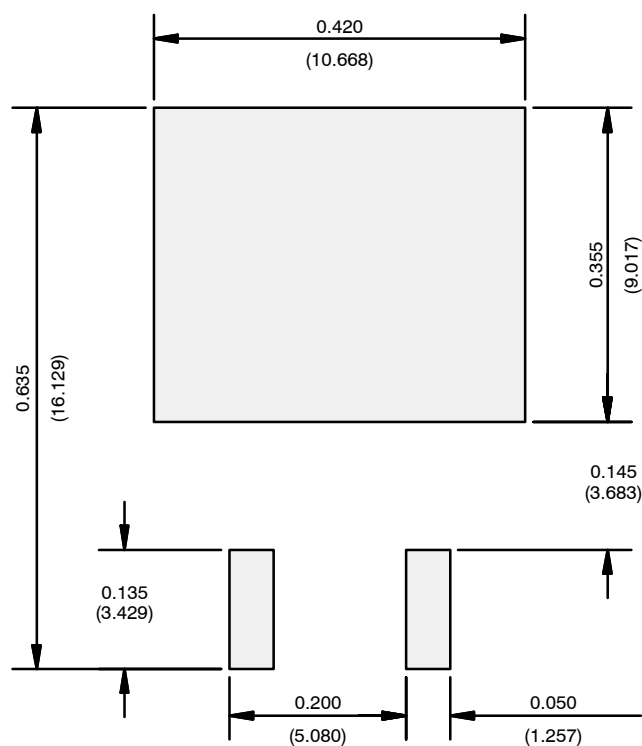
SECTION A-A

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

| DIM. | | INCHES | | MILLIMETERS | |
|---------------------------------|------------|-----------|-------|-------------|--------|
| | | MIN. | MAX. | MIN. | MAX. |
| A | | 0.160 | 0.190 | 4.064 | 4.826 |
| b | | 0.020 | 0.039 | 0.508 | 0.990 |
| b1 | | 0.020 | 0.035 | 0.508 | 0.889 |
| b2 | | 0.045 | 0.055 | 1.143 | 1.397 |
| c* | Thin lead | 0.013 | 0.018 | 0.330 | 0.457 |
| | Thick lead | 0.023 | 0.028 | 0.584 | 0.711 |
| c1 | Thin lead | 0.013 | 0.017 | 0.330 | 0.431 |
| | Thick lead | 0.023 | 0.027 | 0.584 | 0.685 |
| c2 | | 0.045 | 0.055 | 1.143 | 1.397 |
| D | | 0.340 | 0.380 | 8.636 | 9.652 |
| D1 | | 0.220 | 0.240 | 5.588 | 6.096 |
| D2 | | 0.038 | 0.042 | 0.965 | 1.067 |
| D3 | | 0.045 | 0.055 | 1.143 | 1.397 |
| D4 | | 0.044 | 0.052 | 1.118 | 1.321 |
| E | | 0.380 | 0.410 | 9.652 | 10.414 |
| E1 | | 0.245 | - | 6.223 | - |
| E2 | | 0.355 | 0.375 | 9.017 | 9.525 |
| E3 | | 0.072 | 0.078 | 1.829 | 1.981 |
| e | | 0.100 BSC | | 2.54 BSC | |
| K | | 0.045 | 0.055 | 1.143 | 1.397 |
| L | | 0.575 | 0.625 | 14.605 | 15.875 |
| L1 | | 0.090 | 0.110 | 2.286 | 2.794 |
| L2 | | 0.040 | 0.055 | 1.016 | 1.397 |
| L3 | | 0.050 | 0.070 | 1.270 | 1.778 |
| L4 | | 0.010 BSC | | 0.254 BSC | |
| M | | - | 0.002 | - | 0.050 |
| ECN: T13-0707-Rev. K, 30-Sep-13 | | | | | |
| DWG: 5843 | | | | | |

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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